KK1600-FAST SWITCHING THYRISTOR

1800-2000 V_{DRM}

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HIGH POWER THYRISTOR FOR INVERTER APPLICATION

Features:

. All Diffused Structure
. Amplifying Gate Configuration
. Blocking capability

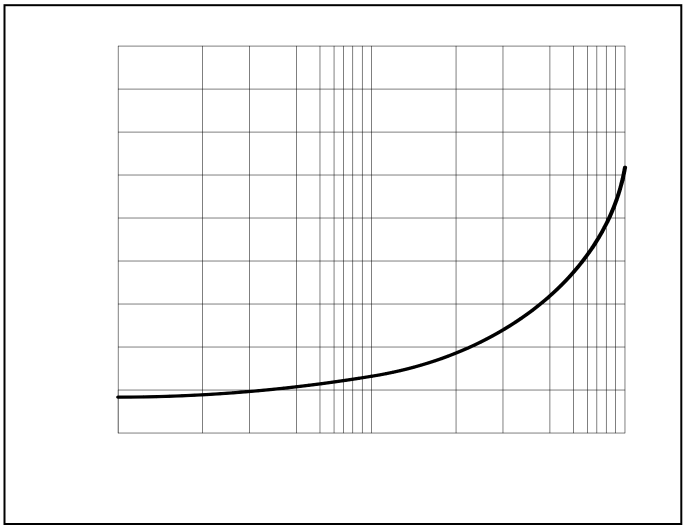
ELECTRICAL CHARACTERISTICS AND RATINGS KK1600-FAST SWITCHING THYRISTOR

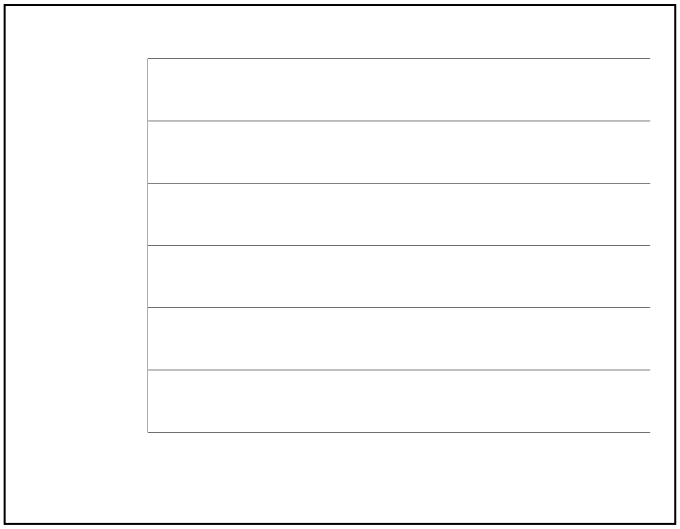
Gating

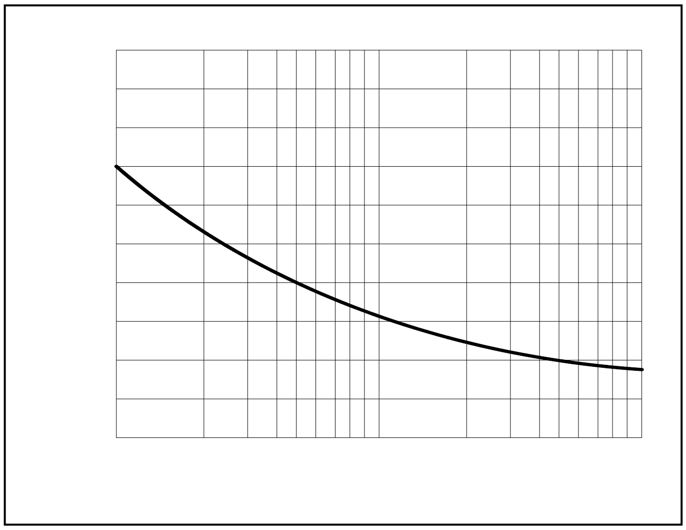
Parameter	**Symbol**	**Min.**	**Max.**	**Typ.**	**Units**	**Conditions**
Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		150		mA	V_D=12V;R_L=3ohms;T_j=+25ºC
Gate- trigger voltage	V_{GT}	0.70	2.5		V	V_D=12V;R_L=3ohms;T_j=+25ºC
Peak negative voltage	V_{GRM}		5		V	

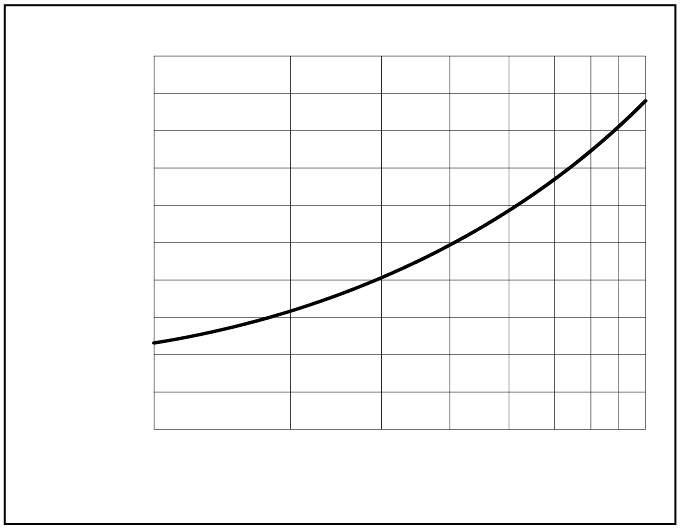
Dynamic

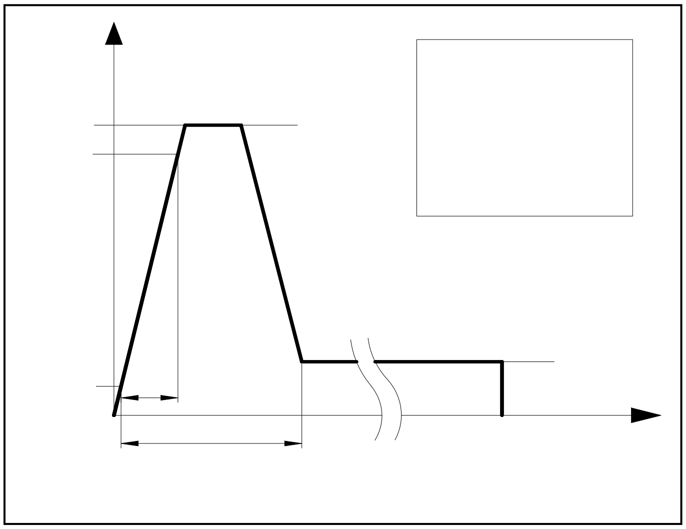
Parameter	**Symbol**	**Min.**	**Max.**	**Typ.**	**Units**	**Conditions**
Delay time	t_d		3.0	2.5	s	I_{TM}=1000A; V_D=67%V_{DRM} Gate pulse: V_G=30V; R_G=10ohms; t_r=0.1 s; t_p=20 s











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